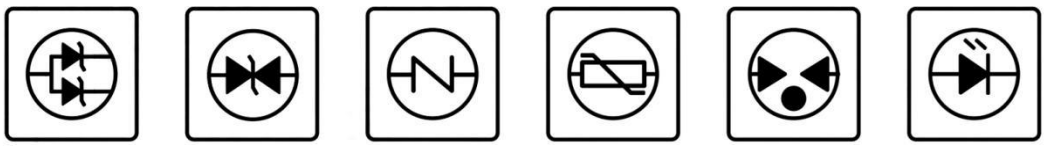
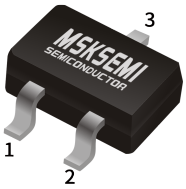
MSKSEMI
SEMICONDUCTOR



Product data sheet

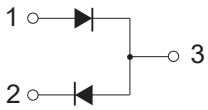


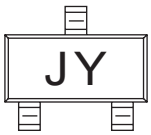
SOT-23

FEATURES

- This Switching Diode has The Following Features:
- Low Leakage Current Applications

Marking: JY





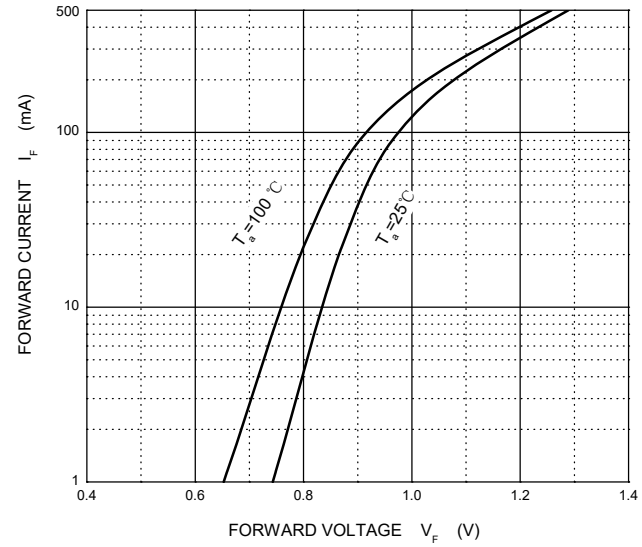
Maximum Ratings @Ta=25℃

Parameter	Symbol	Limit	Unit
Non-Repetitive Peak Reverse Voltage	V_{RM}	70	V
DC Blocking Voltage	V_R	70	V
Forward Continuous Current	I_{FM}	500	mA
Average Rectified Output Current	I_O	215	mA
Non-Repetitive Peak Forward Surge Current @t=8.3ms	I_{FSM}	1.0	A
Power Dissipation	P_D	200	mW
Junction Temperature	T_J	150	℃
Storage Temperature Range	T_{STG}	-55~+150	℃

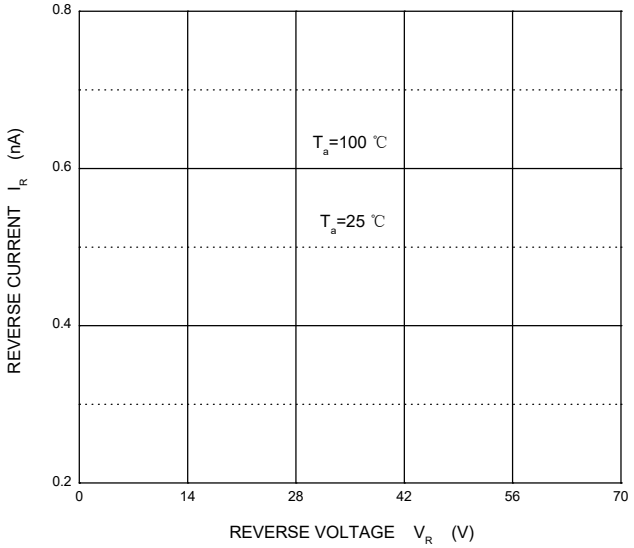
ELECTRICAL CHARACTERISTICS (Ta=25℃ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Max	Unit
Reverse breakdown voltage	$V_{(BR)}$	I_R= 100μA	70		V
Reverse voltage leakage current	I_R	V_R=70V		5	nA
Forward voltage	V_F	I_F=1mA I_F=10mA I_F=50mA I_F=150mA		900 1000 1100 1250	mV
Diode capacitance	C_D	V_R=0, f=1MHz		2	pF
Reverse recovery time	t_{rr}	I_F = I_R=10mA		3	μs

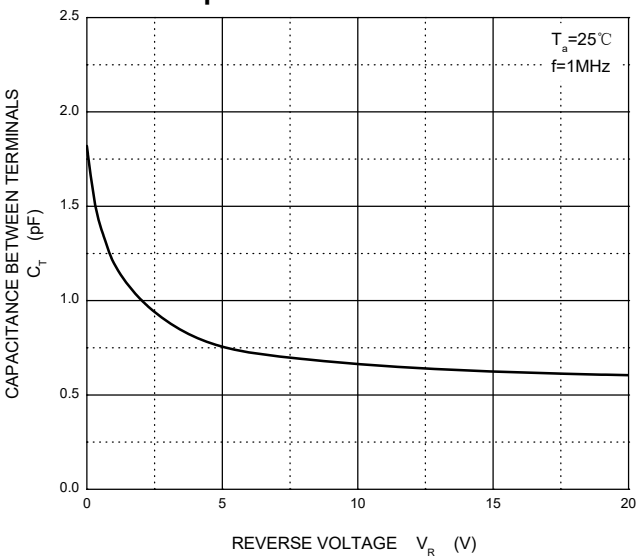
Forward Characteristics



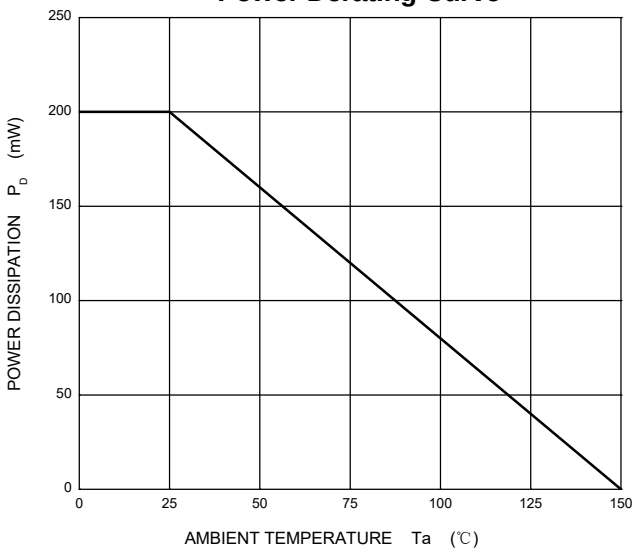
Reverse Characteristics



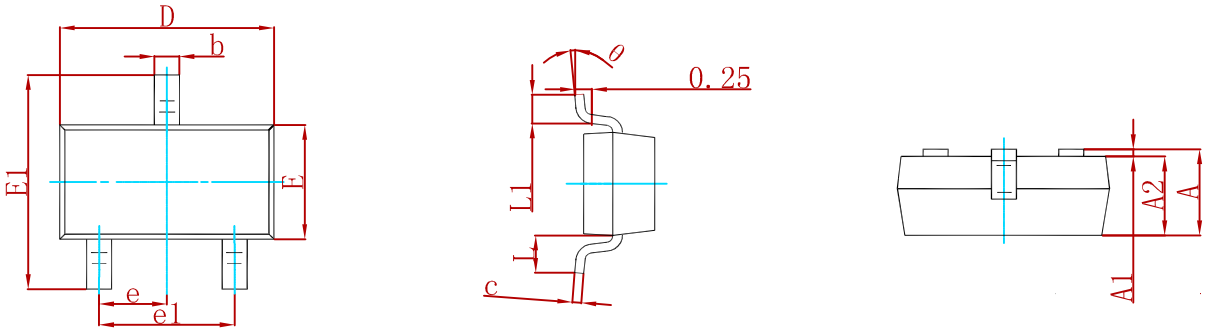
Capacitance Characteristics



Power Derating Curve

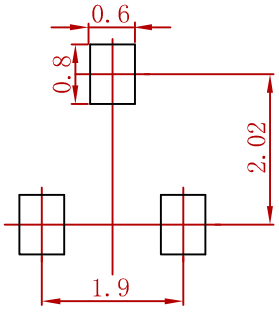


PACKAGE MECHANICAL DATA



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	0.900	1.150	0.035	0.045
A1	0.000	0.100	0.000	0.004
A2	0.900	1.050	0.035	0.041
b	0.300	0.500	0.012	0.020
c	0.080	0.150	0.003	0.006
D	2.800	3.000	0.110	0.118
E	1.200	1.400	0.047	0.055
E1	2.250	2.550	0.089	0.100
e	0.950 TYP		0.037 TYP	
e1	1.800	2.000	0.071	0.079
L	0.550 REF		0.022 REF	
L1	0.300	0.500	0.012	0.020
θ	0°	8°	0°	8°

Suggested Pad Layout



Note:
1.Controlling dimension:in millimeters.
2.General tolerance:± 0.05mm.
3.The pad layout is for reference purposes only.

REEL SPECIFICATION

P/N	PKG	QTY
BAV199	SOT-23	3000

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